



Gallium Nitride (GaN) enables High-Efficient and Bidirectional Auxiliaries – an On-Board Charger Case Study

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GaN On-Board Charger

Agenda

- 1 Motivation**
- 2 Requirements**
- 3 Prototype**
- 4 Commissioning**

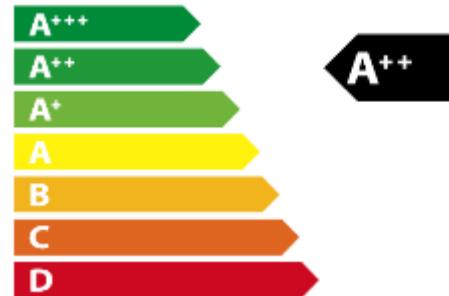
Gallium Nitride (GaN) Technology Promise



It will be cheap



It will be small



It will be efficient

GaN Transistors

Material Properties

- › GaN has unique material and electronic properties due to wide-bandgap

- Low $R_{DS(on)}$

→ Reduced conduction losses



- Low parasitic capacitance

→ Fast switching at low losses



→ High frequency for smaller passive components



- Reverse conduction at low losses (performance similar to SiC Schottky diode)

→ Intrinsic advantage for bidirectional operation



- High temperature operation capability

→ At the moment not in focus due to assembly technology and efficiency targets

GaN Transistors

Semiconductor Manufacturing



GaN power device industry: the supply chain is acting to support market growth

Source: http://www.yole.fr/Power_GaN_SupplyChain_HEMTcomparison.aspx#.Ww8Fmu6FPDc



The GaN market is Estimated to Hit \$2.7 Billion by 2020

Source: <https://www.prnewswire.com/news-releases/the-gan-market-is-estimated-to-hit-27-billion-by-2020-677614283.html>

- › GaN transistors can be grown on standard (and cheap) Si wafers



GaN structures
on standard Si wafer



- › Highly interesting for industry / consumer market due to better efficiency than Si transistors (e.g. power supplies for server farms)

→ Penetration of consumer market will smooth the way for automotive market?

GaN for Power Electronics

Focus Applications

› 48V converter



48V / 12V DCDC

› High voltage converter up to 650V



400V / 12V DCDC



On-Board Charger



48V Inverter



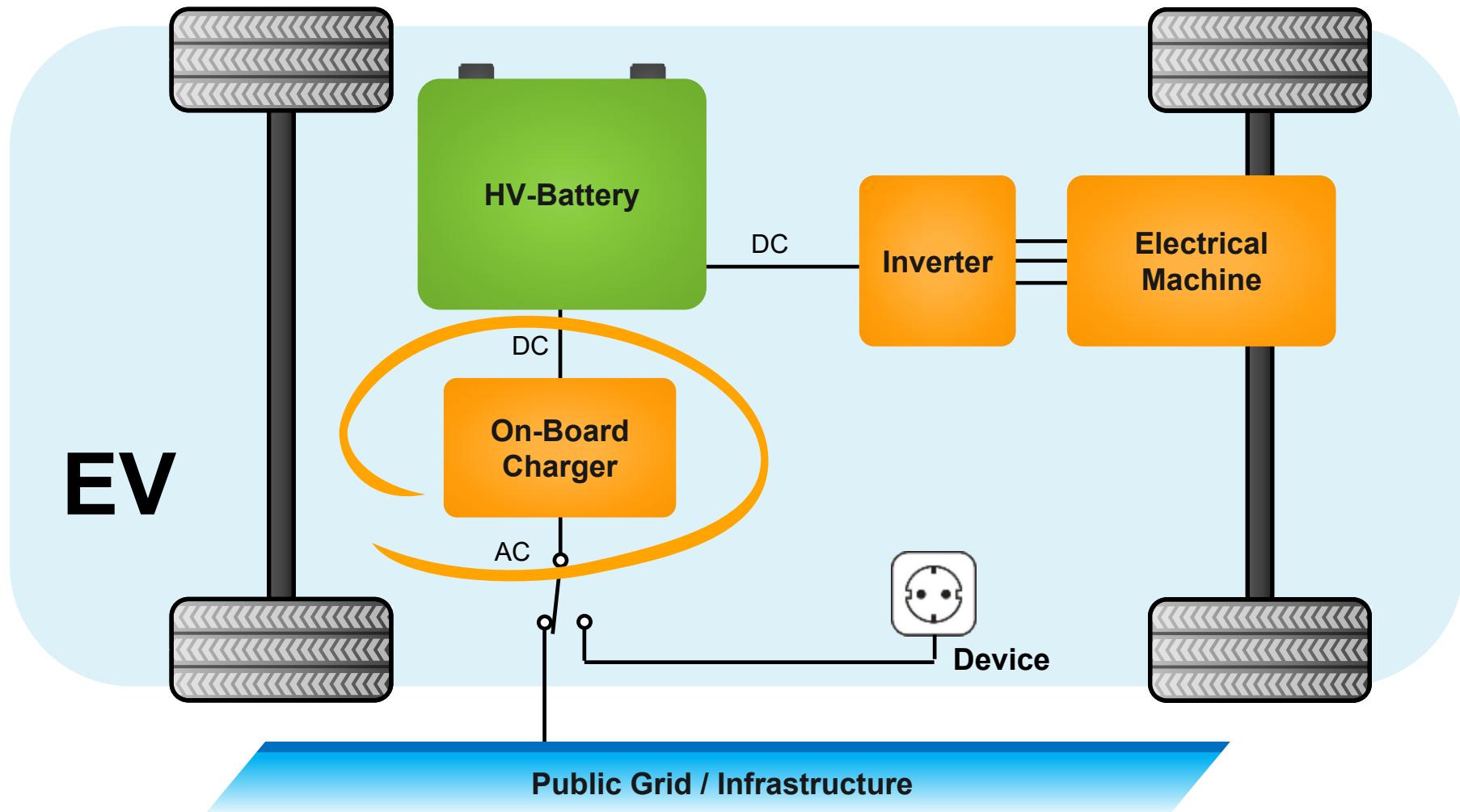
Wireless Charger



400V Inverter

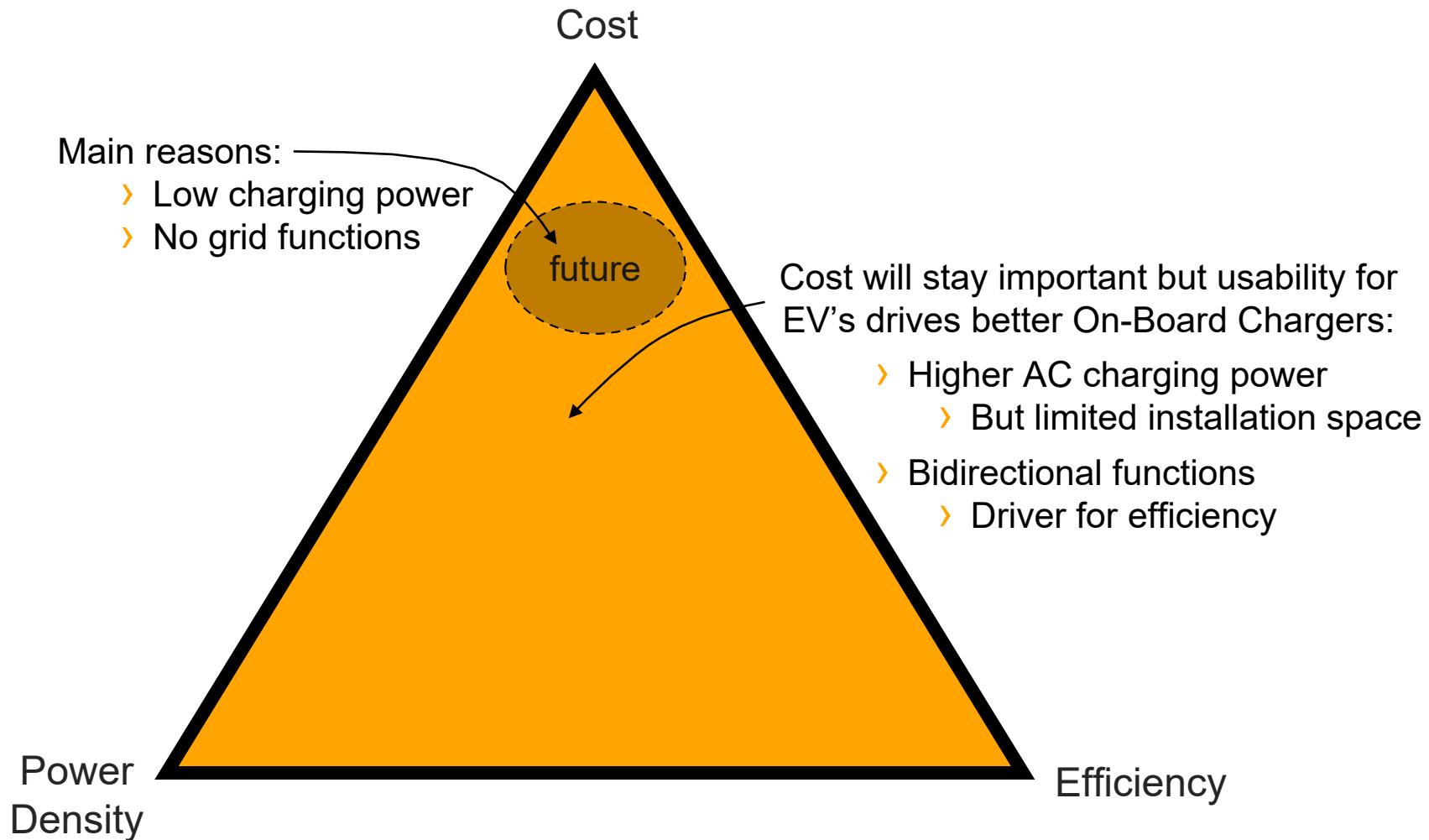
Battery Electric Vehicles

Architecture



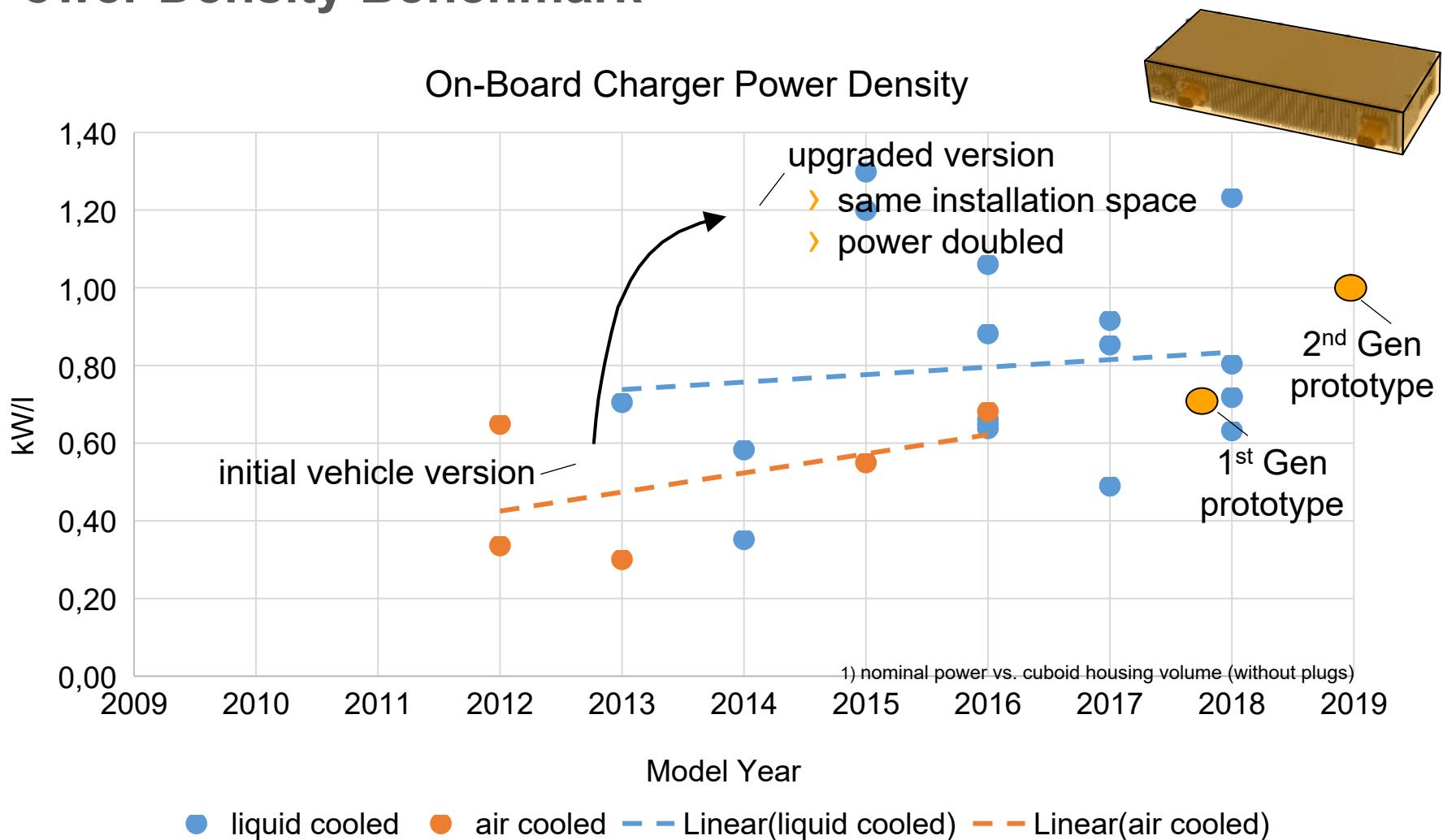
Auxiliaries: On-Board Charger and HV-LV DCDC

Design Corner Points



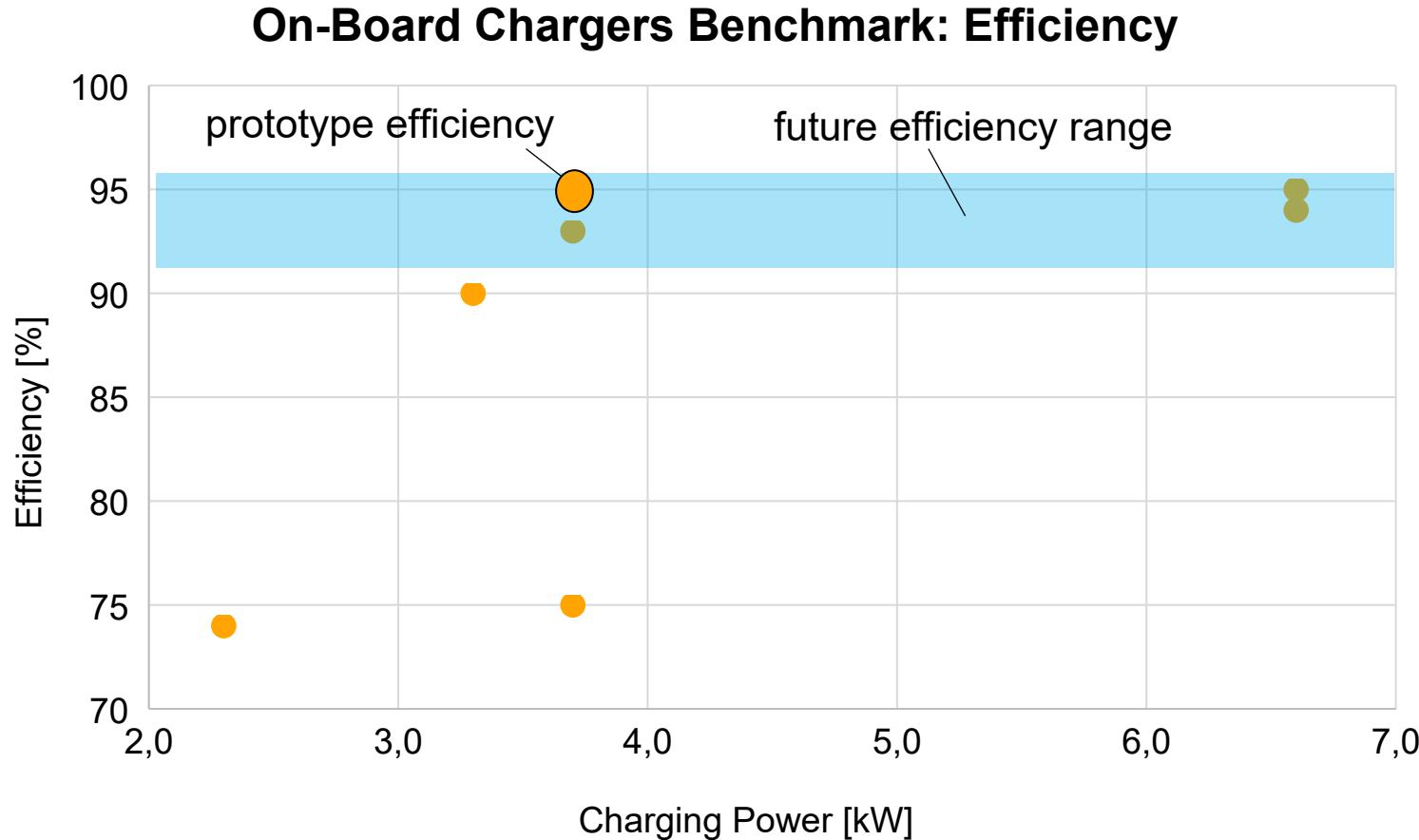
On-Board Chargers

Power Density Benchmark



On-Board Chargers

Efficiency Benchmark



GaN On-Board Charger

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GaN On-Board Charger Laboratory Prototype

Key Requirements

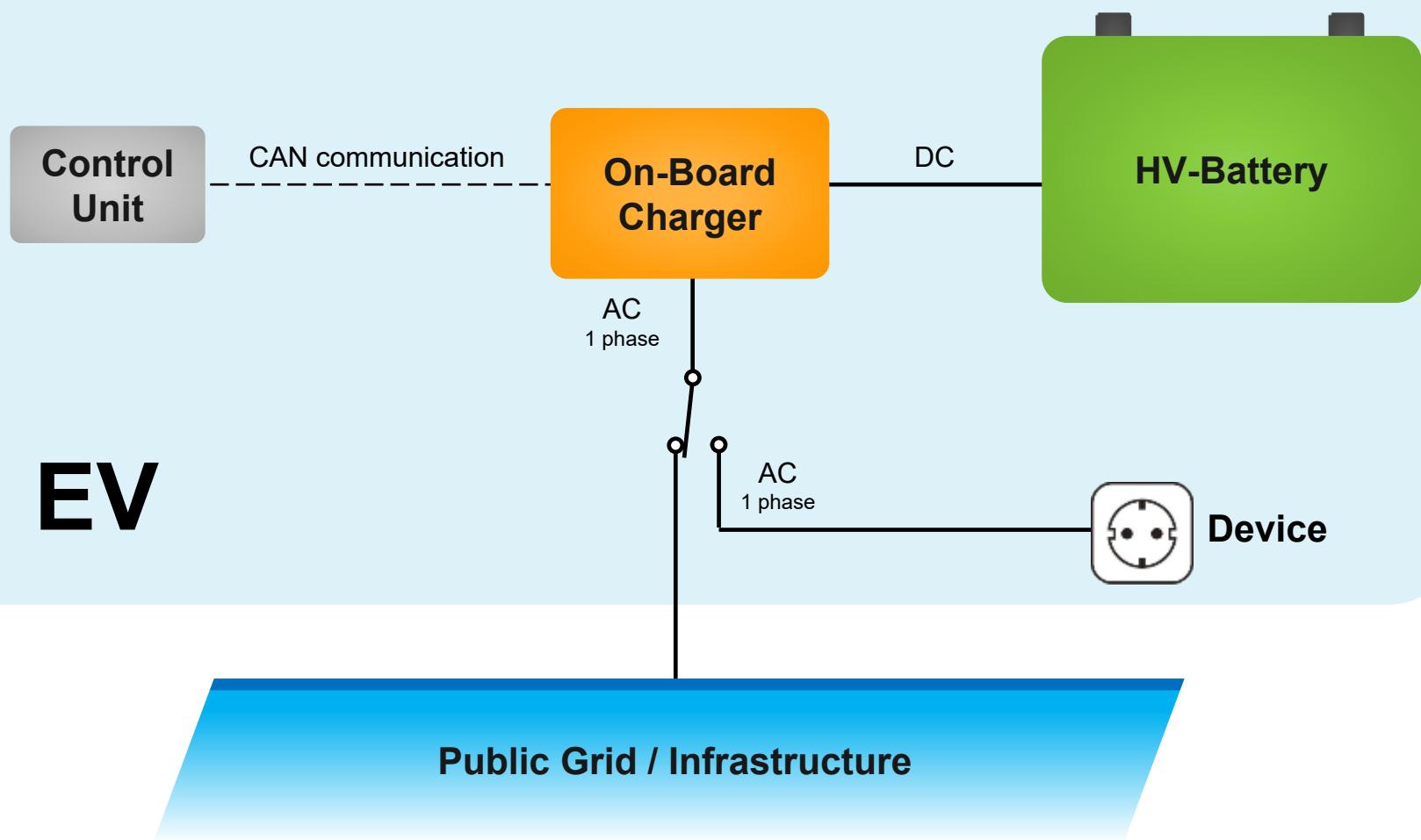
1. Bidirectional: vehicle to grid and vehicle to device
2. Wide-bandgap semiconductor switches: GaN (Gallium Nitride)
3. Air-cooled

Further Technical Specification:

- › Single-phase charger with efficiency up to 95%
- › Galvanically separated
- › Nominal power: 3.7kW ($I_{AC\ max} = 16A_{rms}$)
- › AC Input voltage: $80V_{rms} - 265V_{rms}$
- › Supply frequency: 45Hz – 65Hz
- › Battery voltage: **270V – 470V**
- › Active power factor correction (≥ 0.98)
- › Consideration of EMC standards

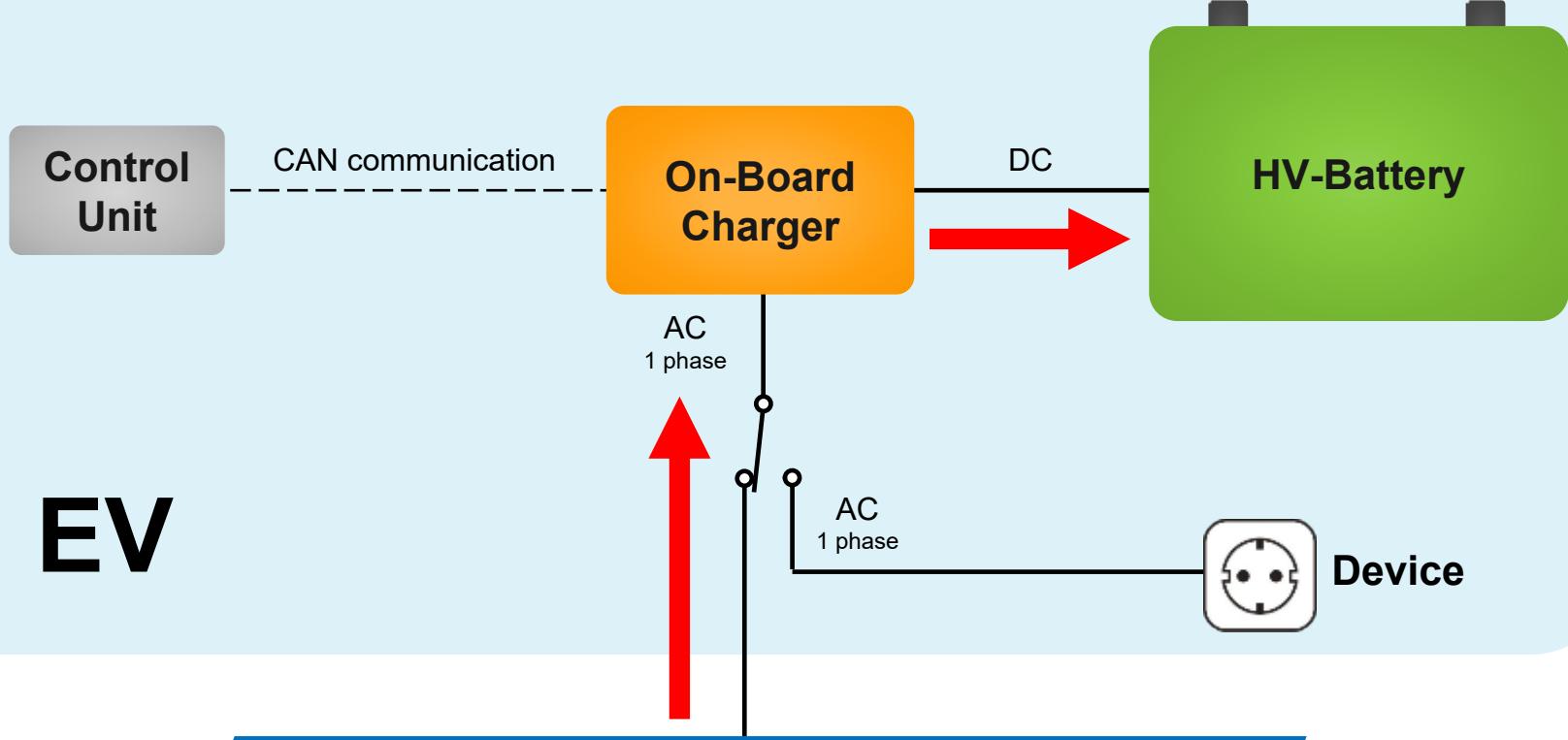
} Compatible with global public grid

GaN On-Board Charger System Overview



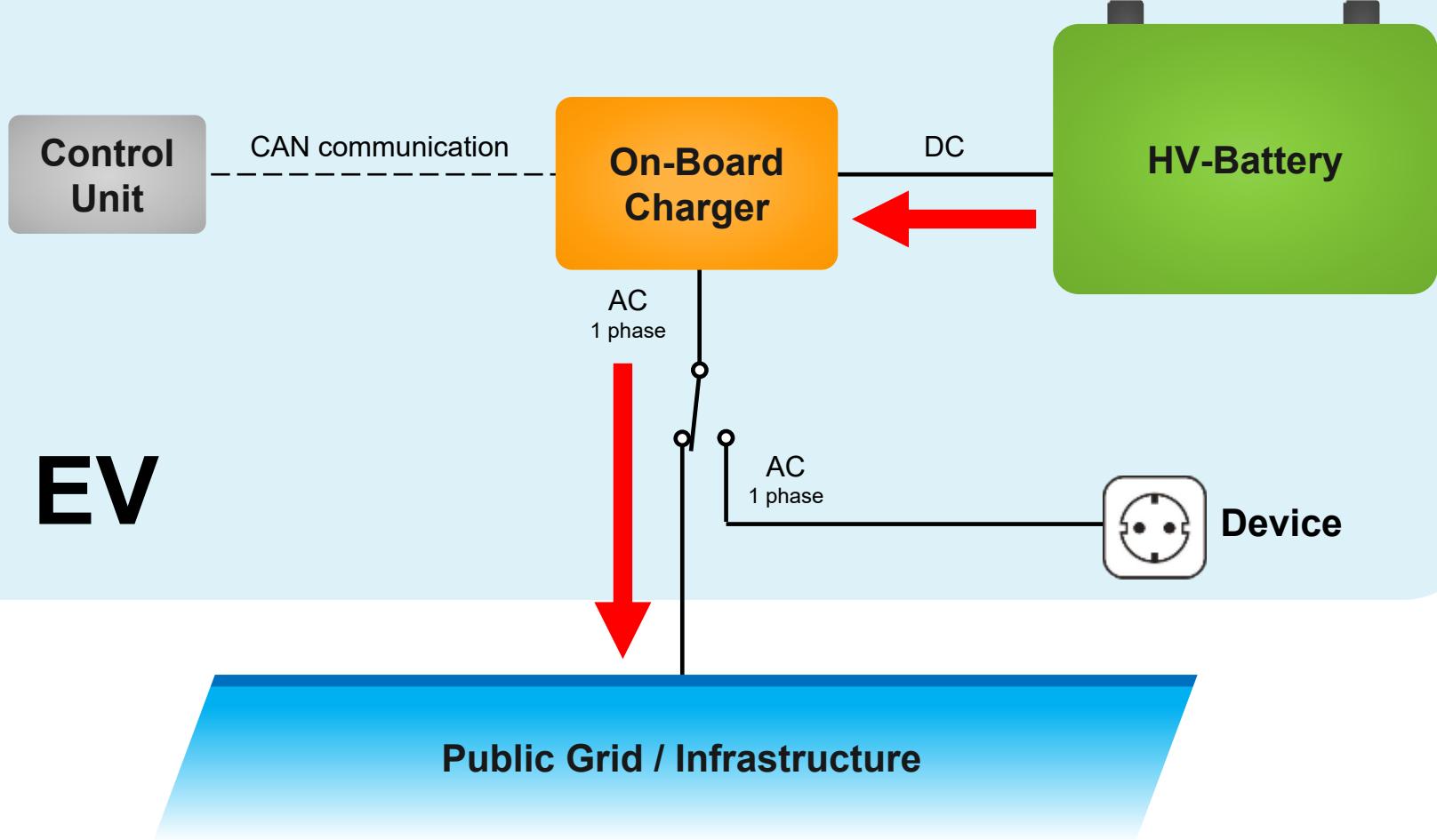
GaN On-Board Charger

AC Charging



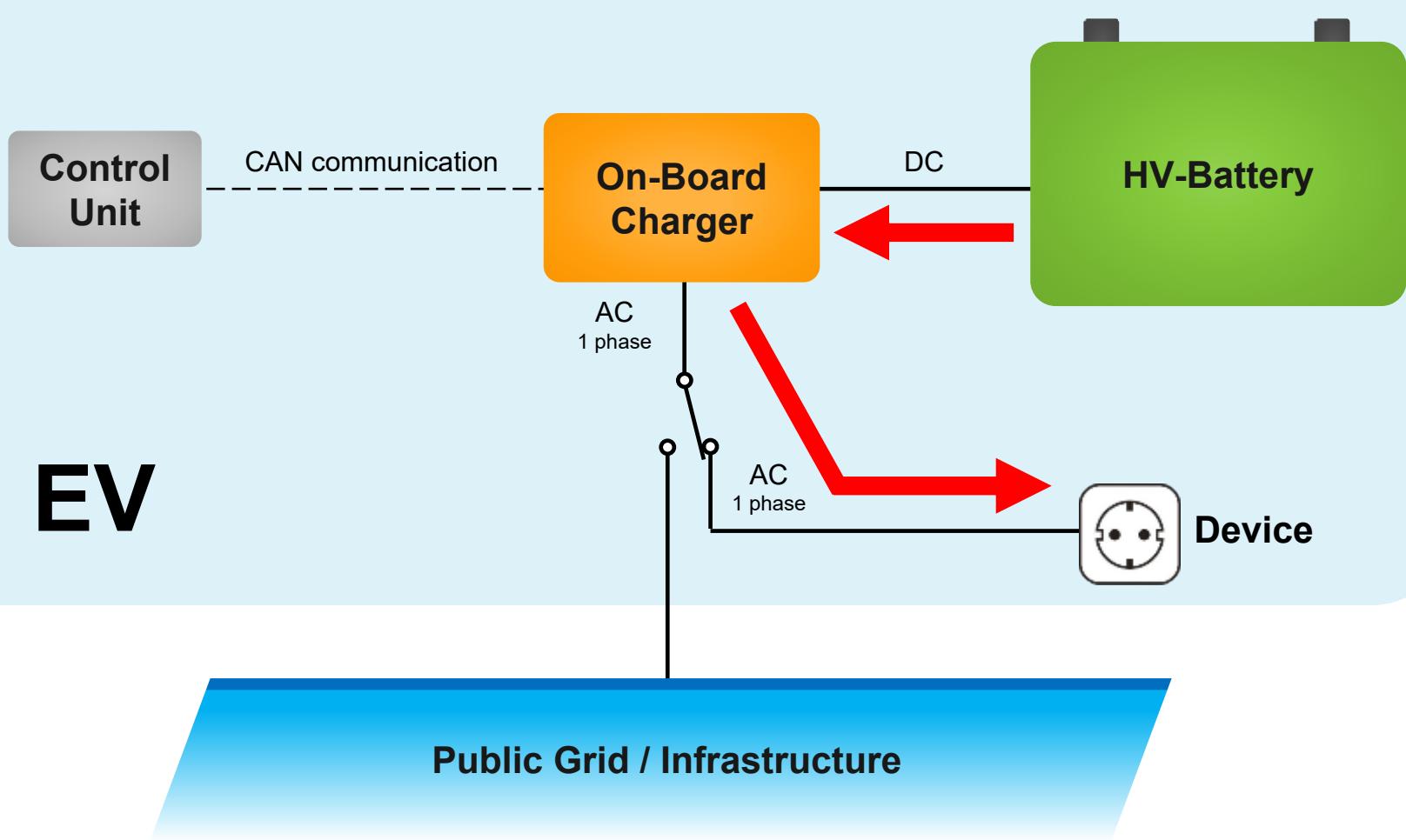
GaN On-Board Charger

Vehicle to Grid (V2G)



GaN On-Board Charger

Vehicle to Device (V2D)



Future Use Cases

Vehicle integrated in Grid

	Not plugged	Charge @ Home	Charge @ Work	Charge @ Shop	Charge @ Rest
Bi-Directional					
Vehicle-2-Device Selection lever on P, 1-ph socket "My car is my office", workshop, camping	✓	✓	✓	✓	✓
Vehicle-2-Home Optimize my energy consumption Black-out back-up		✓			
Vehicle-2-Site Peak load damping Power cost optimization, vehicle swarm			✓		
Vehicle-2-Grid Mains stabilization Mega vehicle swarm, protocol, payment	✓	✓	✓	✓	✓

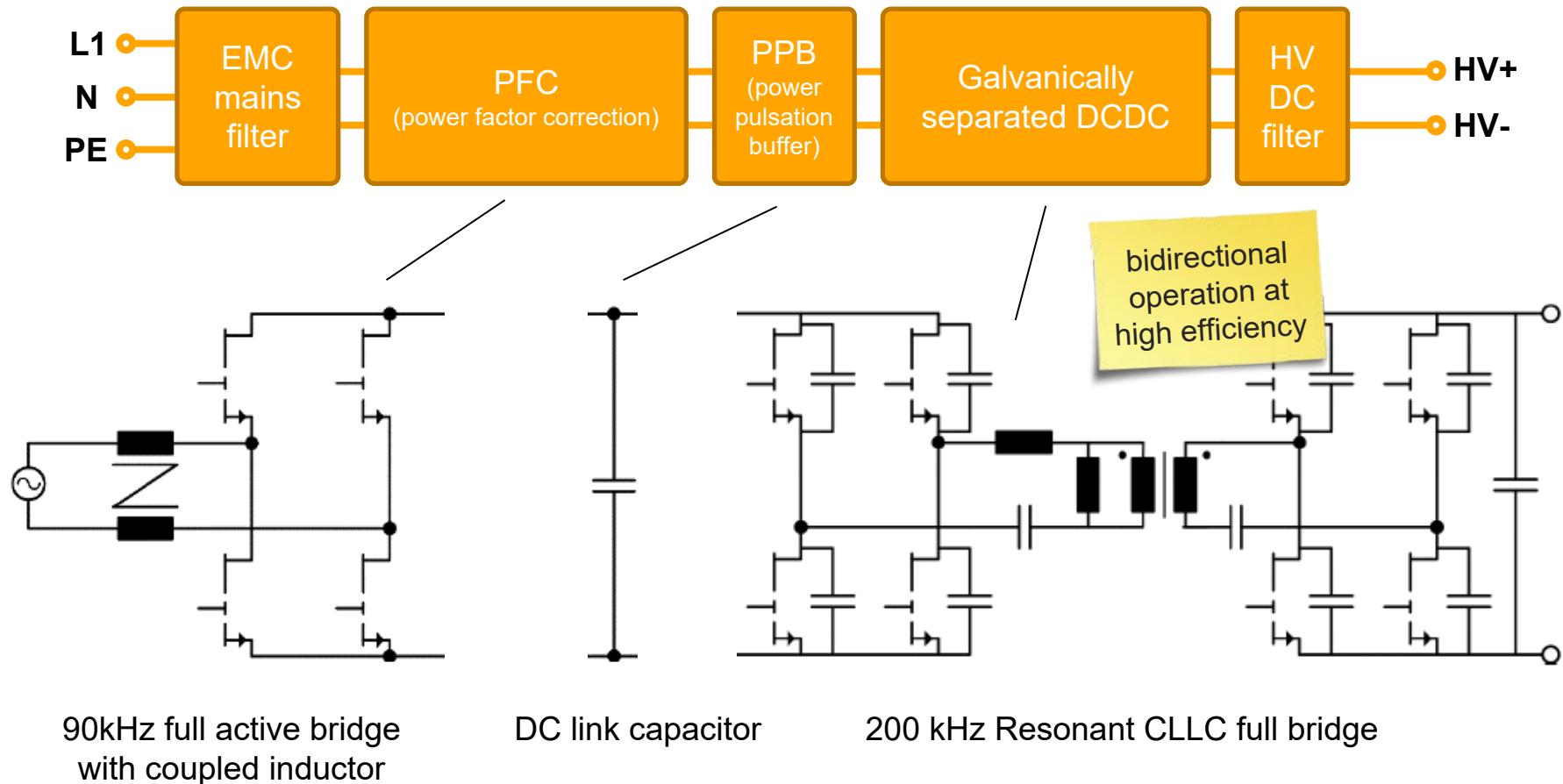
GaN On-Board Charger

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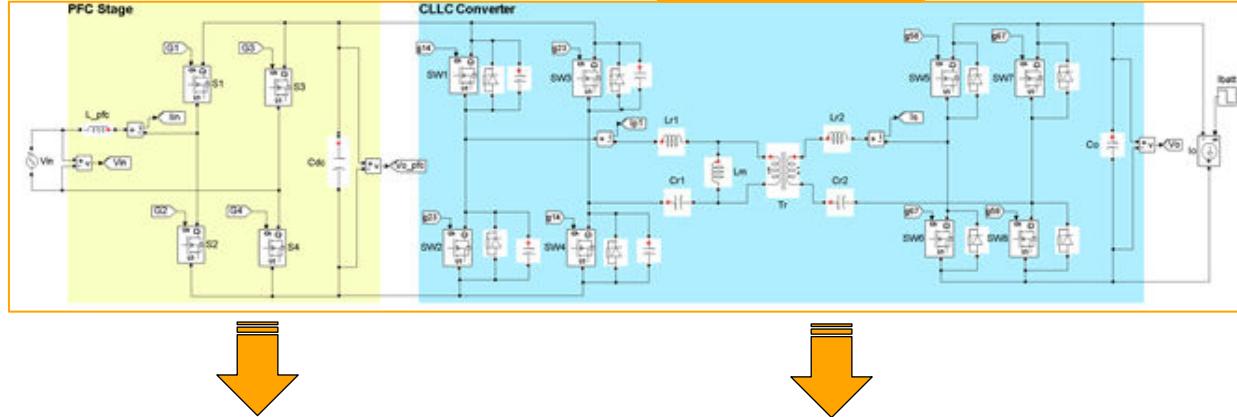
GaN On-Board Charger

Bidirectional Charger Topology

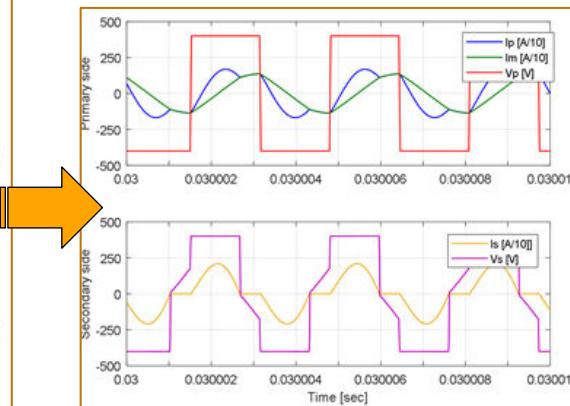
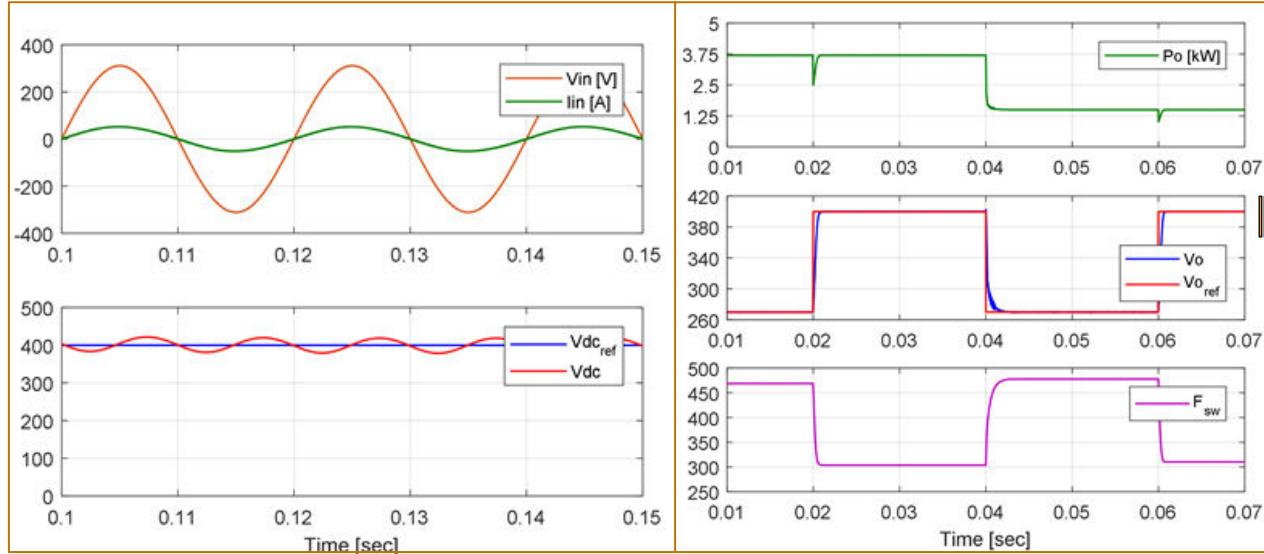
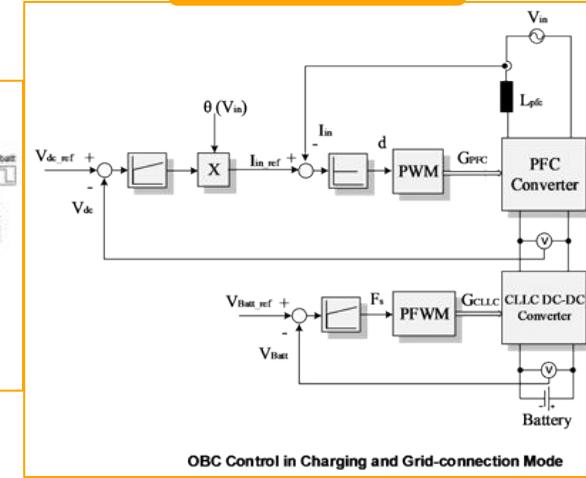


GaN On-Board Charger Simulation

MATLAB Model



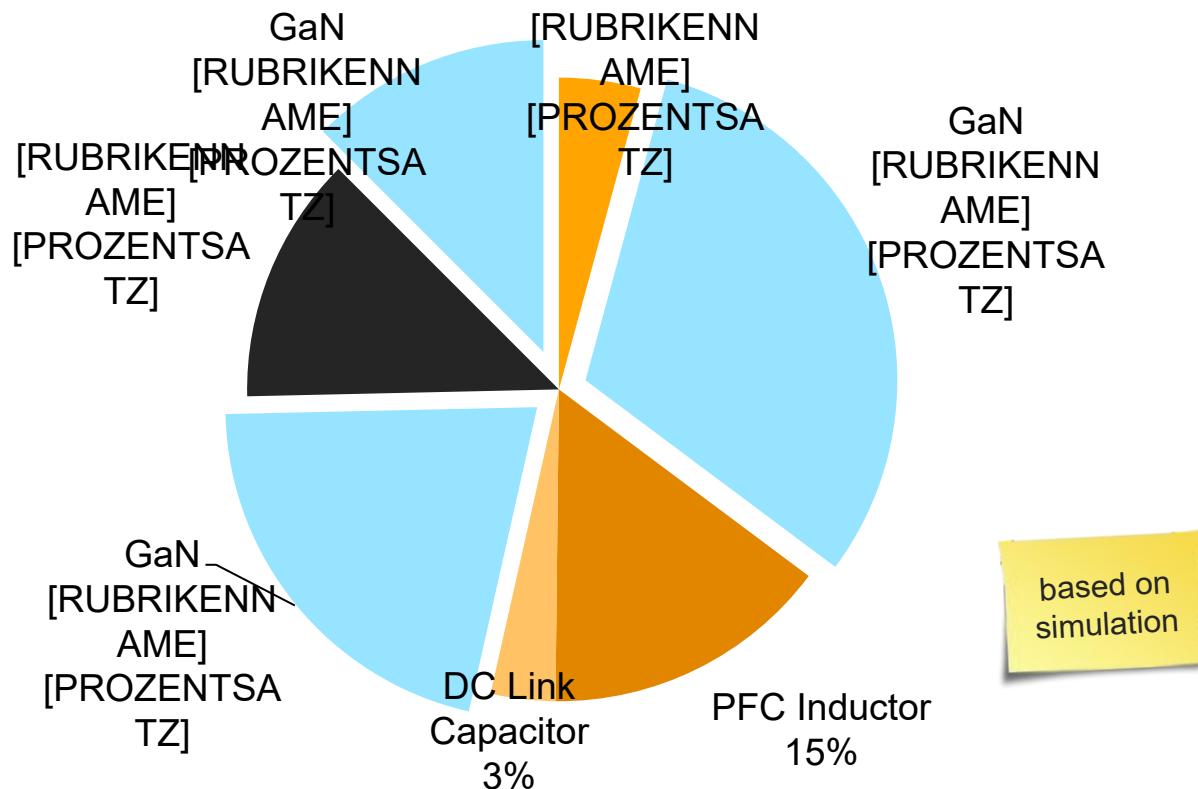
Control Algorithm



GaN On-Board Charger

66% Power Dissipated by Semiconductors

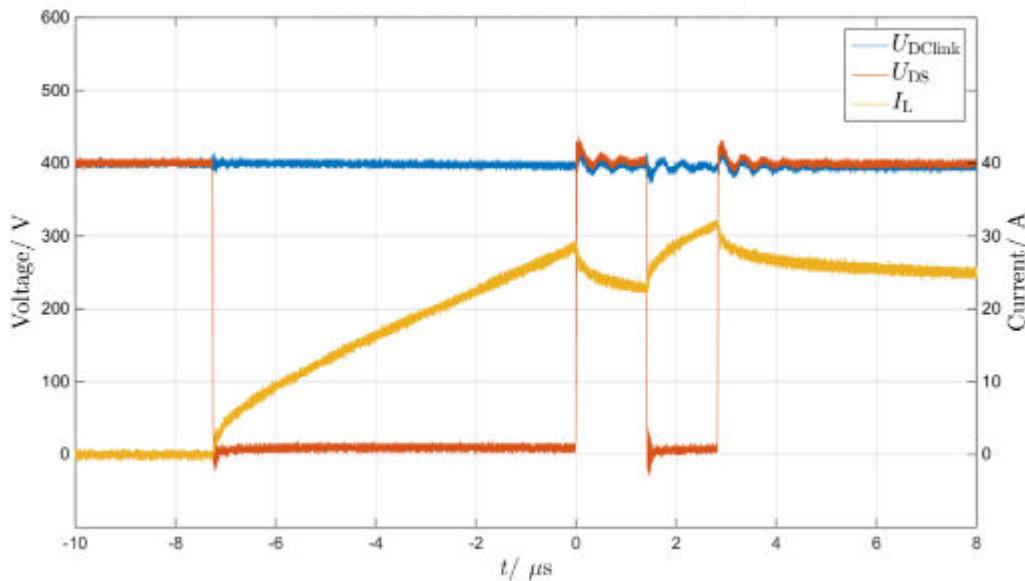
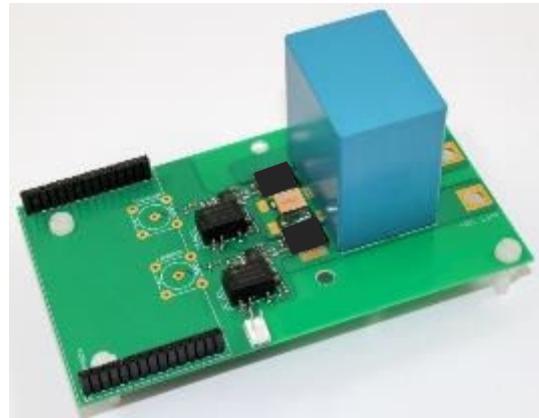
- › Improved transistors (e.g. GaN HEMTs) are good lever for increasing efficiency



GaN Transistors

Double Pulse Test: GaN 7 times faster than Silicon

- Transistor: 650V; 25mΩ
- Half-bridge with low-inductive PCB layout
- Fast slew rates at small voltage overshoot



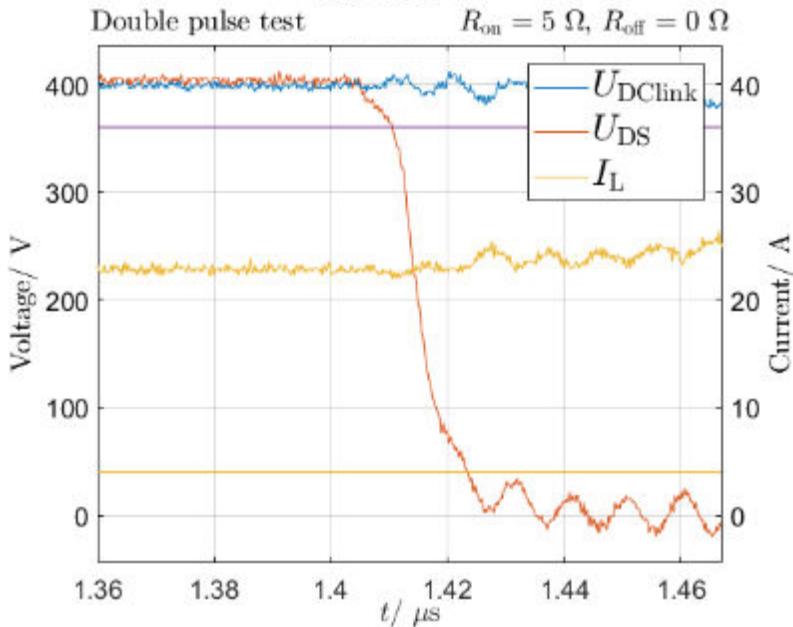
double pulse test board

Turn on resistance	Turn on [kV/μs]	Turn off [kV/μs]
0 Ω	39	37
2 Ω	38	36
5 Ω	25	37
10 Ω	21	37

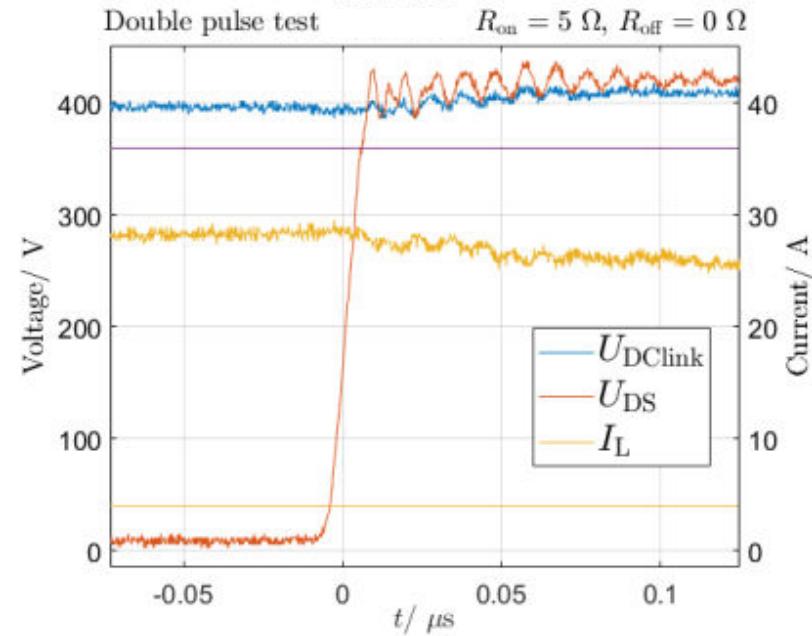
$V_{DC} = 400V$; Turn off resistance = 0 Ω

GaN Transistors

Double Pulse Test: Small Overvoltage, Small Ringing



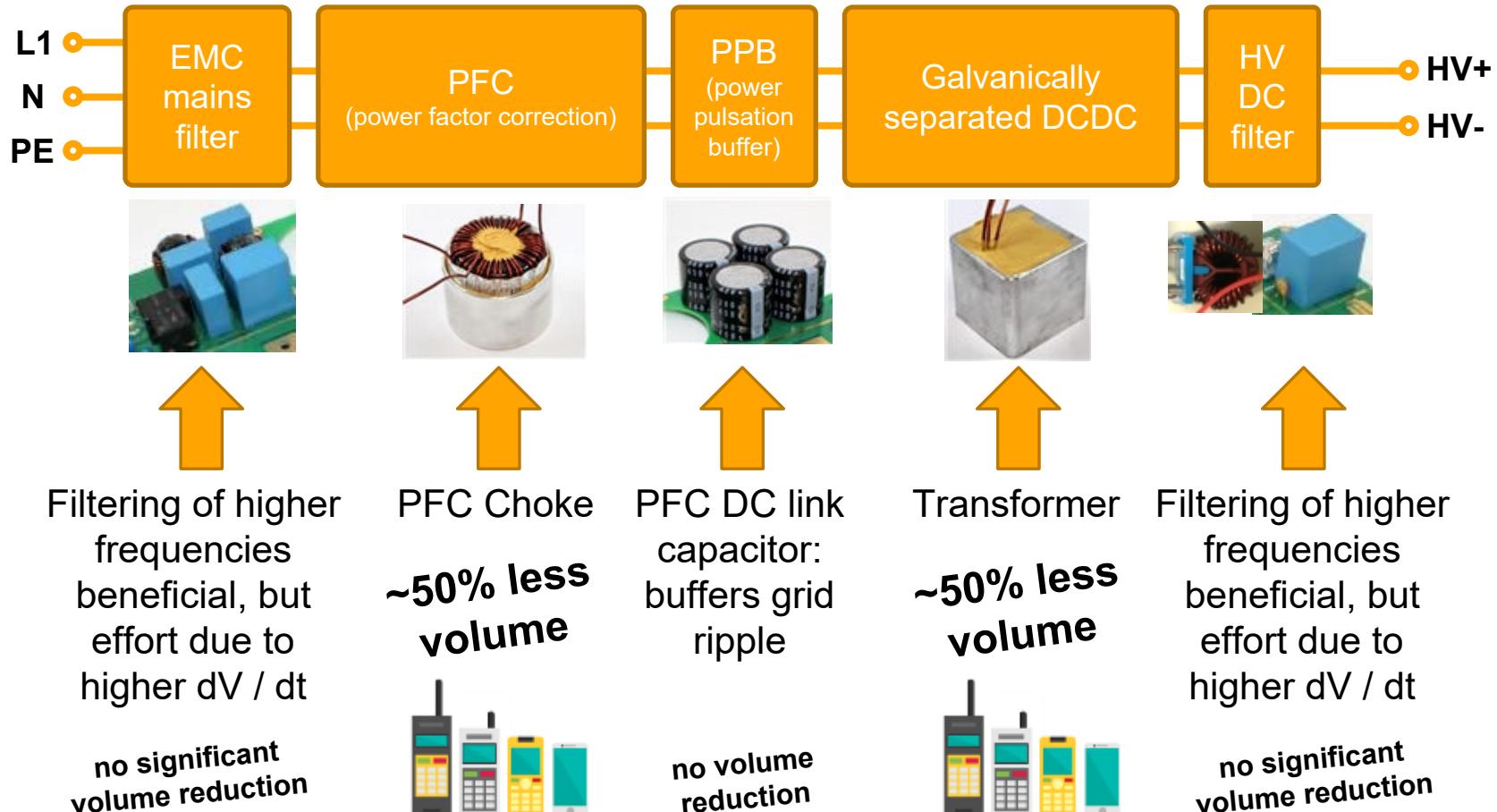
› Turn-on @ $V_{\text{DC}} = 400\text{V}$



› Turn-off @ $V_{\text{DC}} = 400\text{V}$

Power Density

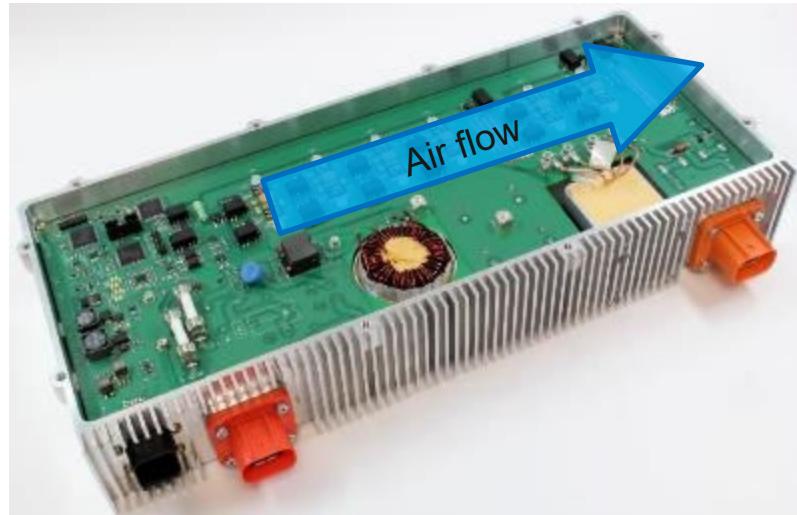
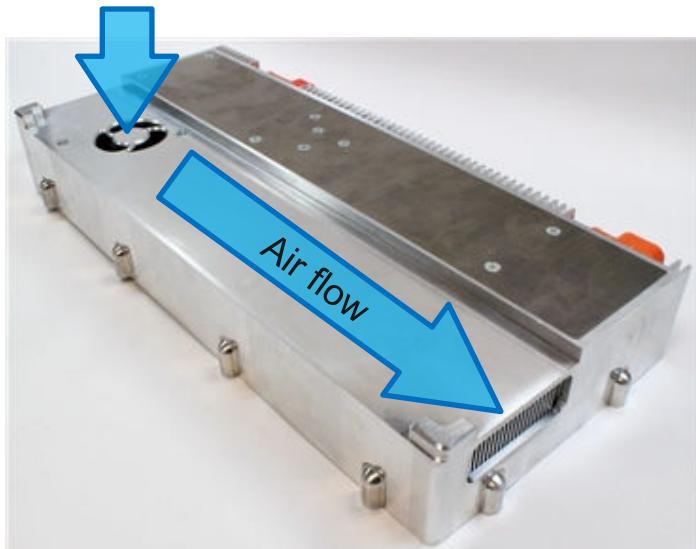
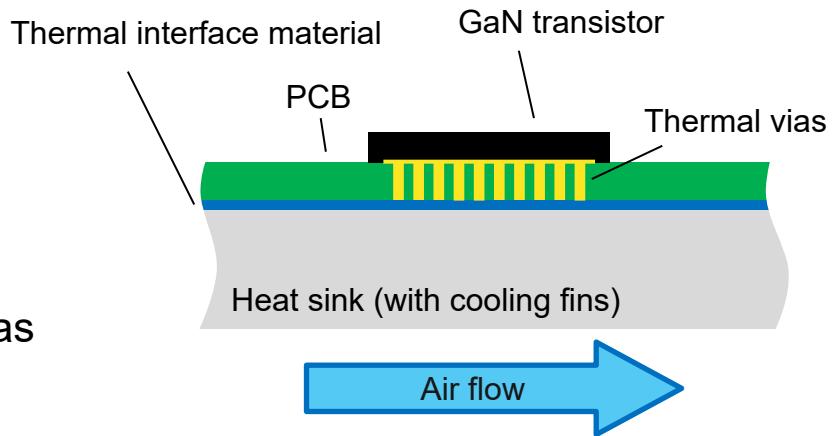
Component Impact by High Switching Frequency



GaN On-Board Charger

Cooling Concept: Simple and Integration friendly

- › Air-cooled
- › Bottom-side cooling
- › Standard PCB: 1.6mm, 8 layers, FR4
- › Heat transfer to heat sink through thermal vias
- › Fan power consumption max. 4W



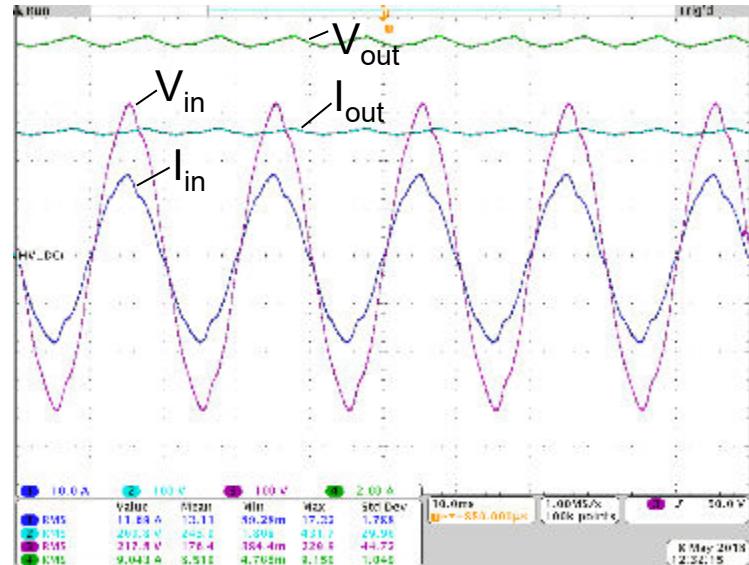
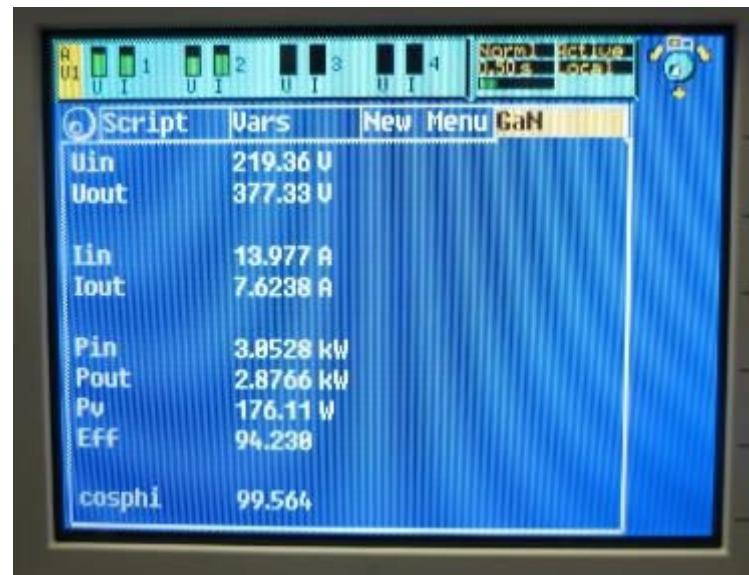
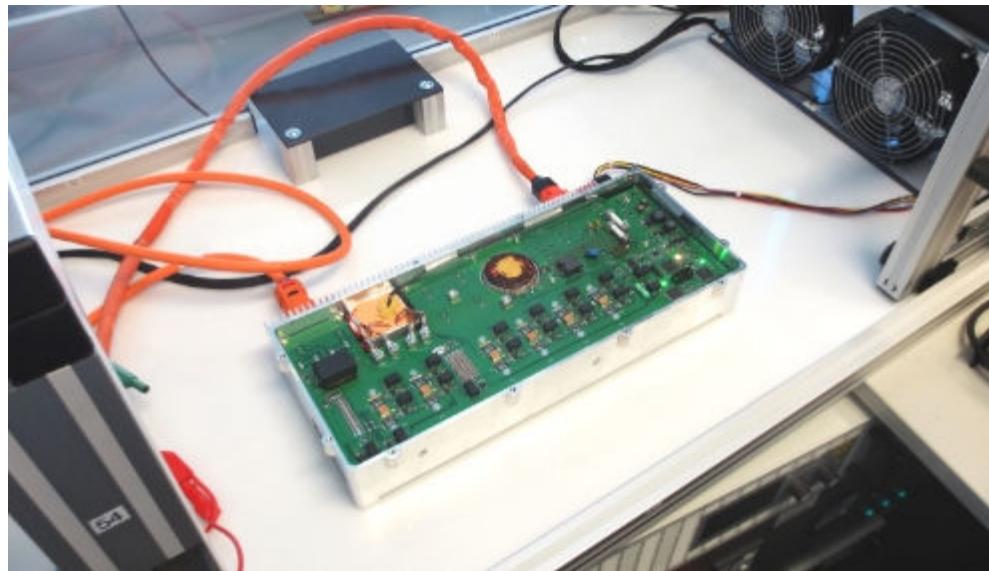
GaN On-Board Charger

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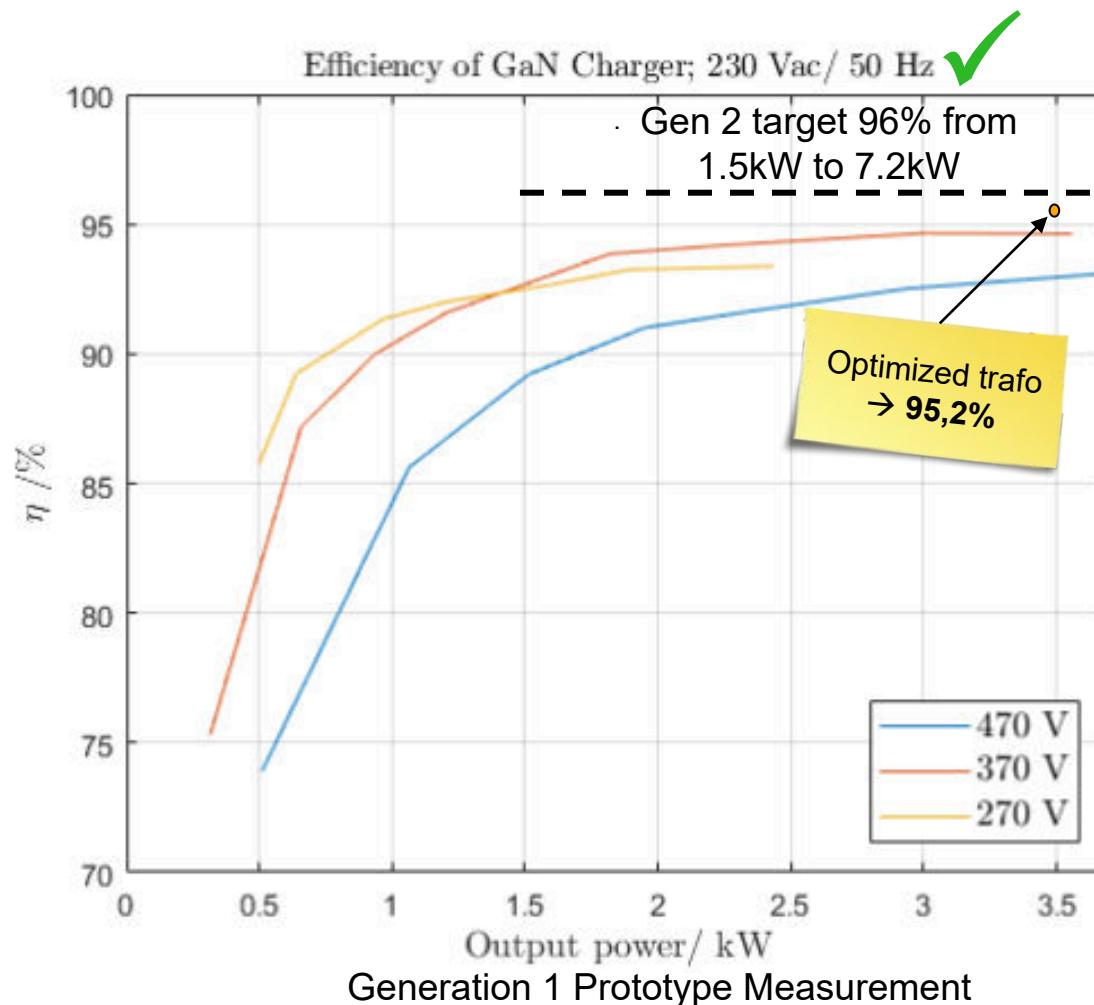
GaN On-Board Charger Commissioning

- › Charging mode at $\sim 220\text{V}_{\text{rms}}$ AC input voltage
- › Preparation for EMC measurements



GaN On-Board Charger

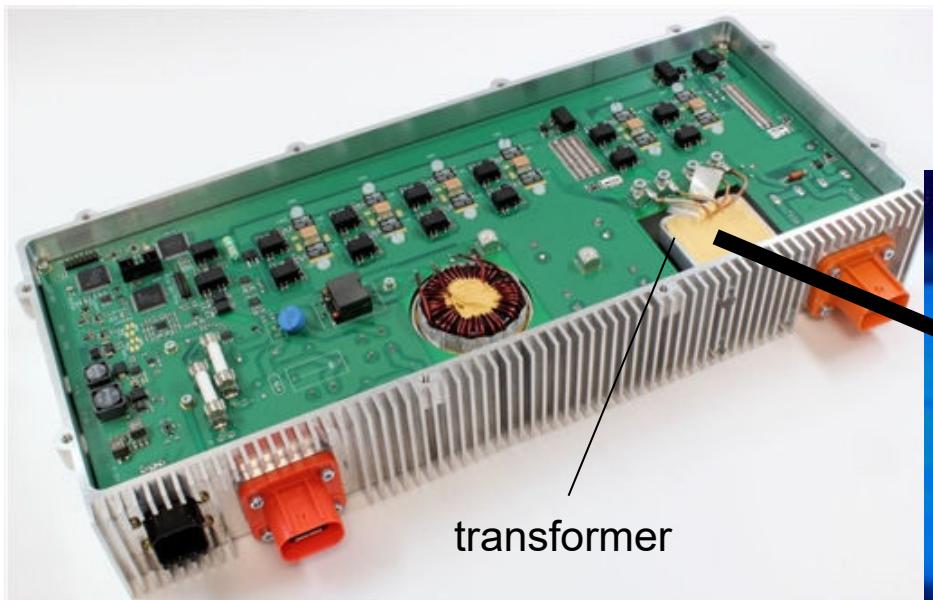
Efficiency measurements meet Expectations



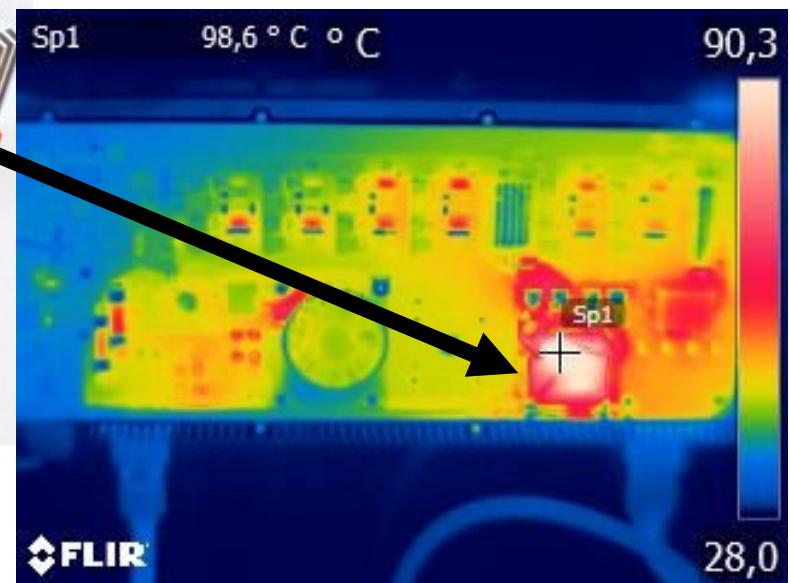
GaN On-Board Charger

Commissioning: High Frequency Challenge for Passives

- › GaN semiconductors thermally stable – passive components more challenging
- › E.g. transformer operating at its limit due to fast switching



Operation up to
900kHz switching
frequency



GaN On-Board Charger

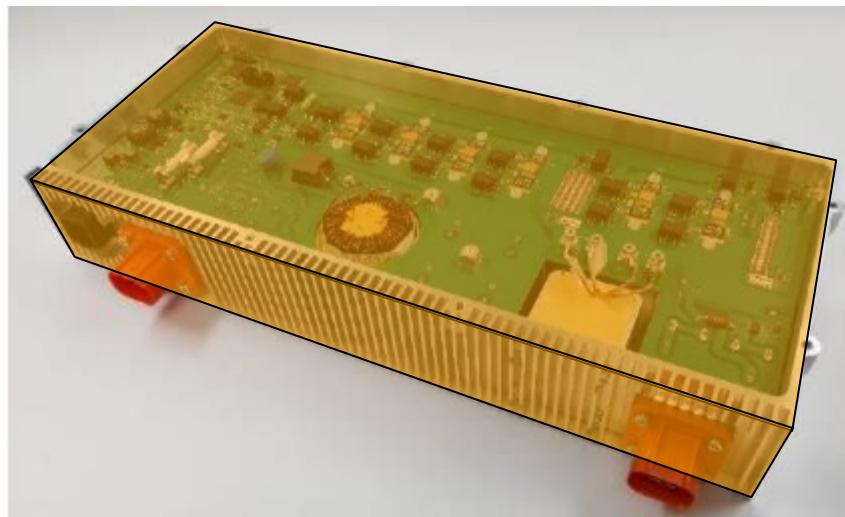
Power Density

- › 3.7kW (V_{out} 270V to 470V)
- › Cooling: air

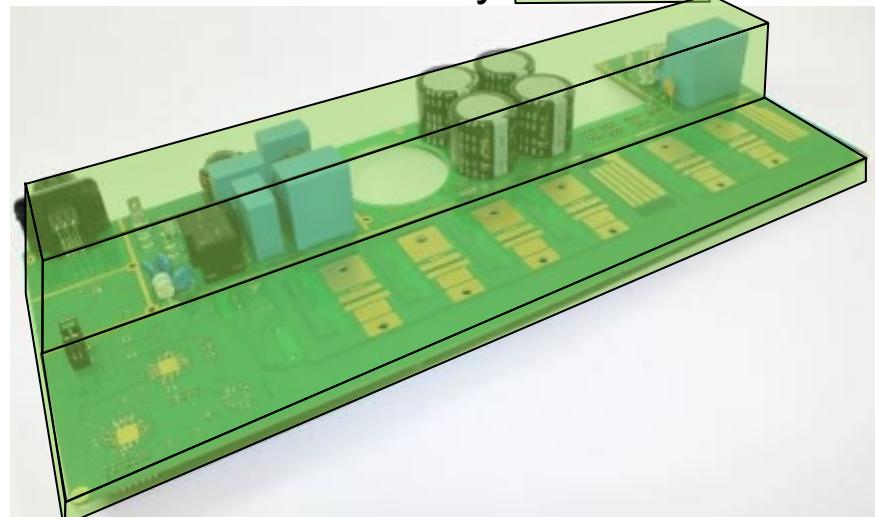
First bidirectional prototype with ~15% improved volume to state of the art air-cooled

Outlook: power density and efficiency to match water-cooled state of the art 1kW/l

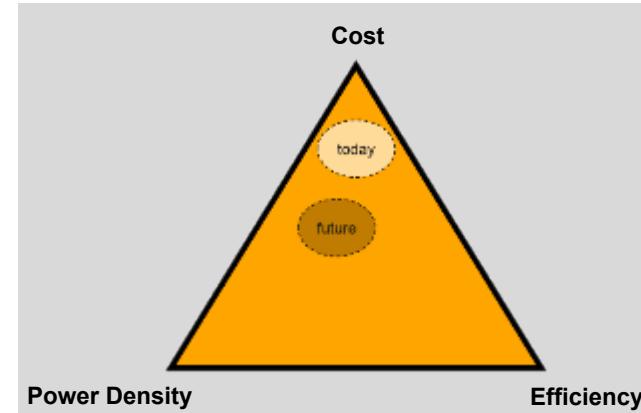
Power density: 0.7kW/l



Power density: 1.7kW/l



Conclusion GaN



- › **Focus on Auxiliaries:** first use case **GaN On-Board Charger** prototype
- › **Bidirectional and air-cooled in same package as liquid cooled and unidirectional**
- › **GaN transistors** good lever for increasing **power density** and **efficiency**
- › Due to high switching frequency: **passive components** additional **challenge** to GaN
- › Future On-Board Charger with **enhanced functionality**: high charging power, bidirectionality
- › **Design trade-off** between **volume, cost and efficiency enabled by GaN**

Yes, we GaN!

